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AMENDMENTS TO THE CLAIMS:

Please cancel claim 32 without prejudice or disclaimer.

Claims 1-20. (Canceled)

Claim 21. (Currently amended) A method for manufacturing a group III nitride compound semiconductor device, comprising:

forming a resist layer on a group III nitride compound semiconductor in a wafer;
patterning said resist layer; and

irradiating a surface of said a wafer with ultraviolet rays to thereby clean a resist residue from said surface of said wafer, said surface comprising said a group III nitride compound semiconductor,

wherein said ultraviolet rays cause a reaction of oxygen molecules to form stimulated oxygen atoms having a strong oxidative power at said surface of said wafer, and

wherein said irradiating said surface of said wafer is performed after said patterning said resist layer.

Claim 22. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said ultraviolet rays have a central wavelength of 172 nm.

Claim 23. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said ultraviolet rays are emitted from an excimer lamp.

Claim 24. (Canceled)

Claims 25 - 30. (Canceled)

Claim 31. (Previously presented) A method for manufacturing a group III nitride

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compound semiconductor device according to claim 21, wherein said stimulated oxygen atoms oxidize an organic contamination on said surface of said wafer into CO, CO₂ and H₂O which flies up from said surface .

Claim 32. (Canceled)

Claim 33. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said group III nitride compound semiconductor comprises a p-type semiconductor, and said irradiating said surface comprises irradiating a surface of said p-type semiconductor to clean a resist residue from said surface of said p-type semiconductor.

Claim 34. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said oxygen molecules are supplied to said surface of said wafer by supplying an oxygen-containing gas to said surface.

Claim 35. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said irradiating said surface of said wafer comprises locating said wafer in an area of an ultraviolet lamp unit which emits said ultraviolet rays.

Claim 36. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said irradiating said surface of said wafer comprises irradiating an entirety of said surface of said wafer.

Claim 37. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said irradiating said surface of said wafer comprises using said ultraviolet rays to cut a molecular chain of said resist residue, and reacting said stimulated oxygen atoms with said cut molecular chain to decompose said resist residue.

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Claim 38. (Currently amended) A method for manufacturing a group III nitride compound semiconductor device, comprising:

forming a resist layer on said group III nitride compound semiconductor;

patterning said resist layer; and

irradiating a surface of said group III nitride compound semiconductor with ultraviolet rays to remove a resist residue from said surface,

wherein said irradiating said surface is performed after said patterning said resist layer, and

wherein said ultraviolet rays:

cut a molecular chain of said resist residue; and

cause a reaction of oxygen molecules to form stimulated oxygen atoms having a strong oxidative power at said surface, said stimulated oxygen atoms reacting with said cut molecular chain to decompose said resist residue.

39. (Previously presented) The method of claim 38, wherein said surface of said group III nitride compound semiconductor comprises a light-transmissible metal electrode formed thereon.

40. (Previously presented) The method of claim 39, wherein said light-transmissible metal electrode comprises an alloy comprising cobalt and gold.

41. (Currently amended) The method of claim 38, further comprising:

~~forming a resist layer on said group III nitride compound semiconductor;~~

~~patterning said resist layer; and~~

supplying said oxygen molecules to said surface of said wafer by supplying an oxygen-containing gas to said surface,

~~wherein said irradiating said surface is performed after said patterning said resist layer,~~

wherein said ultraviolet rays have a central wavelength of 172 nm and are emitted from an excimer lamp,

wherein said stimulated oxygen atoms oxidize an organic contamination on said

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surface of said wafer into CO, CO₂ and H₂O which flies up from said surface,

wherein said group III nitride compound semiconductor comprises a p-type semiconductor, and said irradiating said surface comprises irradiating a surface of said p-type semiconductor to clean a resist residue from said surface of said p-type semiconductor, and

wherein said irradiating said surface of said wafer comprises irradiating an entirety of said surface of said wafer.

42. (New) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said irradiating said surface of said wafer comprises irradiating a surface of said group III nitride compound semiconductor.

43. (New) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, further comprising:

supplying said oxygen molecules to said surface of said wafer by supplying an oxygen-containing gas to said surface.